Description

The VSM17N10 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features
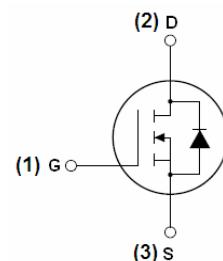
● V_{DS} =100V,I_D =17A

$R_{DS(ON)}$ < 70mΩ @ V_{GS}=10V   (Typ:56mΩ)

$R_{DS(ON)}$ < 85mΩ @ V_{GS}=4.5V   (Typ:65mΩ)

● High density cell design for ultra low Rdson

● Fully characterized avalanche voltage and current

● Good stability and uniformity with high E_{AS}

● Excellent package for good heat dissipation

● Special process technology for high ESD capability

Application

● Power switching application

● Hard switched and high frequency circuits

● Uninterruptible power supply

TO-220C

Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM17N10-TC	VSM17N10	TO-220C	-	-	-

Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	17	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	12	A
Pulsed Drain Current	I_{DM}	60	A
Maximum Power Dissipation	P_D	55	W
Single pulse avalanche energy [Note 5]	E_{AS}	250	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case(Note 2)	$R_{\theta JC}$	2.27	℃/W

Electrical Characteristics (T_C=25℃ unless otherwise noted)
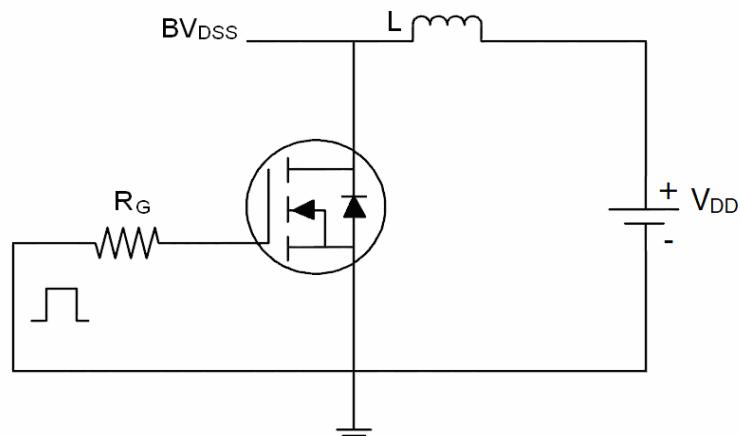
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	110	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5A	-	56	70	mΩ
		V_{GS}=4.5V, I_D=3A		65	85	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=5A	12	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{Iss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	1350	-	PF
Output Capacitance	C_{oss}		-	240	-	PF
Reverse Transfer Capacitance	C_{rss}		-	180	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=2A,R_L=15Ω V_{GS}=10V,R_G=2.5Ω	-	13.8	-	nS
Turn-on Rise Time	t_r		-	9.3	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	43.8	-	nS
Turn-Off Fall Time	t_f		-	11.4	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=5A, V_{GS}=10V	-	30		nC
Gate-Source Charge	Q_{gs}		-	6.4	-	nC
Gate-Drain Charge	Q_{gd}		-	8.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=17A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	17	A
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:
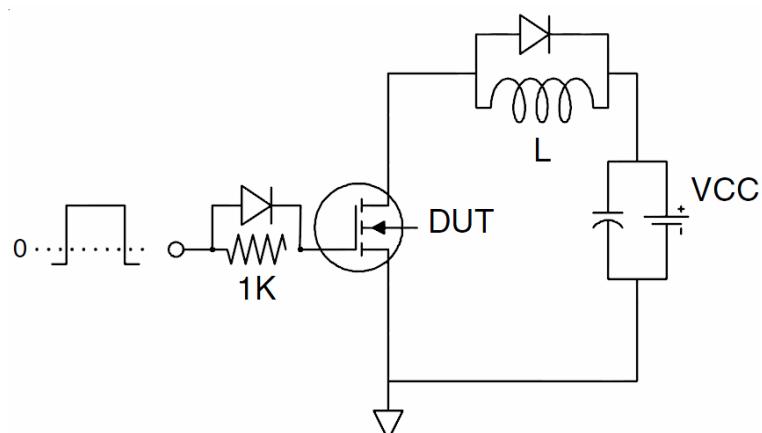
1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

5. EAS condition：Tj=25℃,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25Ω

Test Circuit
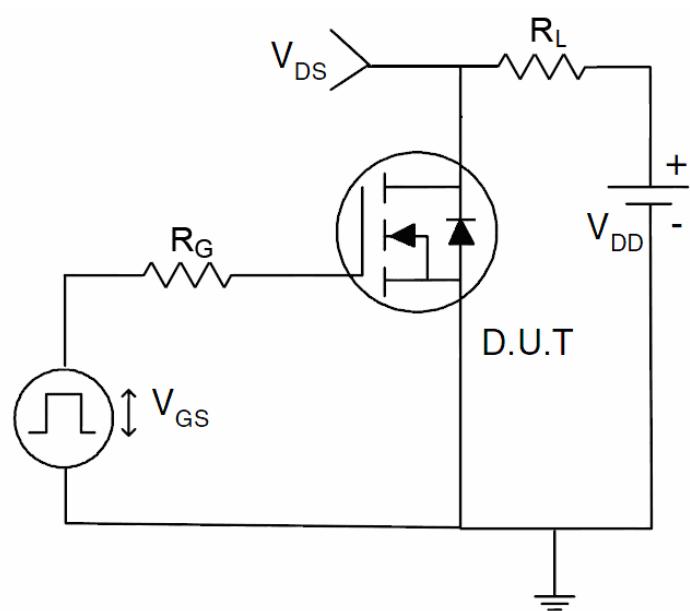
1) E_{AS} test Circuit

2) Gate charge test Circuit

3) Switch Time Test Circuit

Typical Electrical and Thermal Characteristics (Curves)
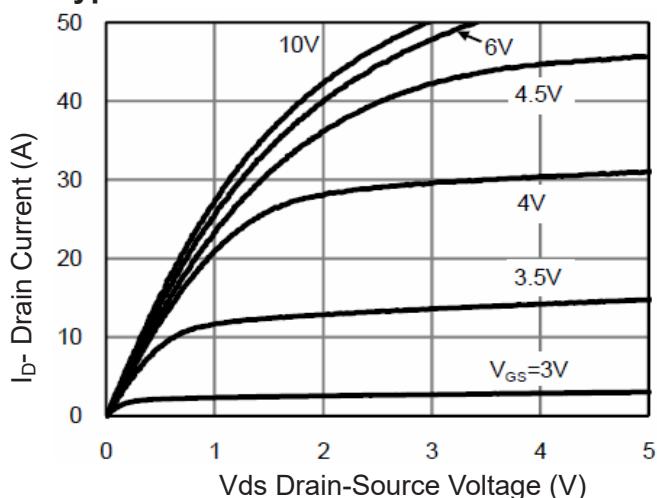
**Figure 1 Output Characteristics**
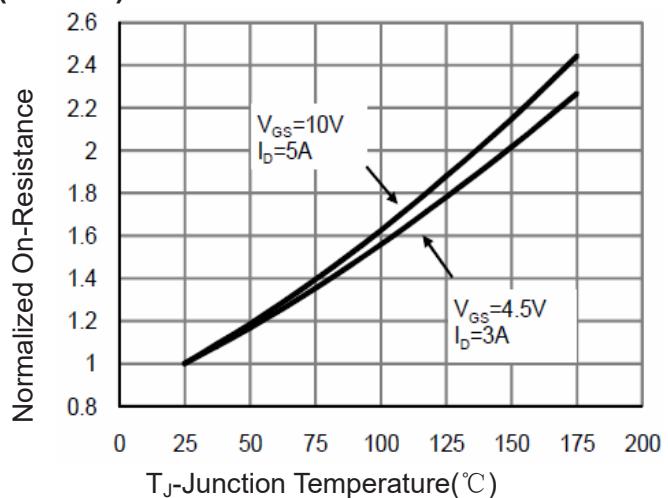
Figure 4 Rdson-JunctionTemperature
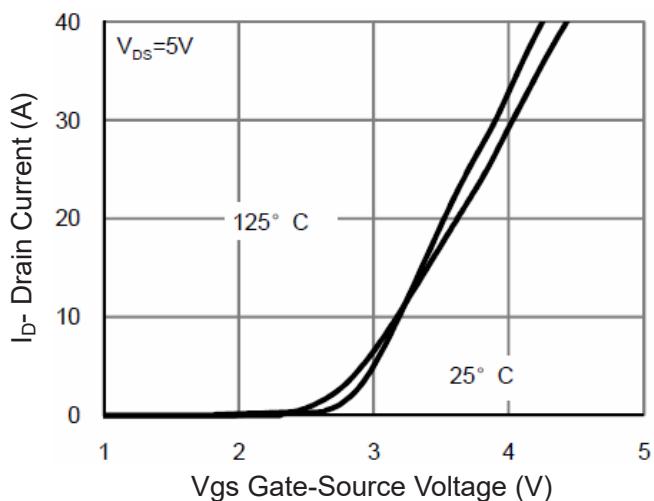
Figure 2 Transfer Characteristics
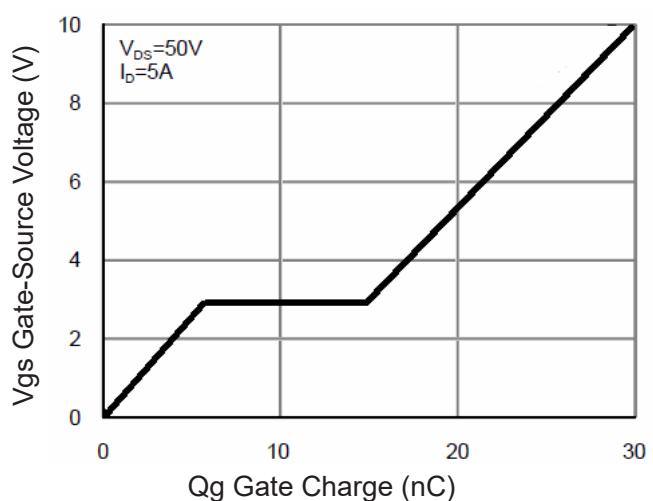
**Figure 5 Gate Charge**
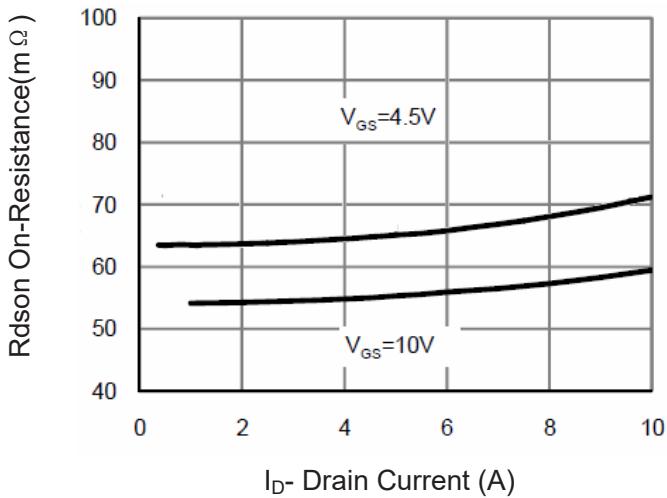
Figure 3 Rdson- Drain Current
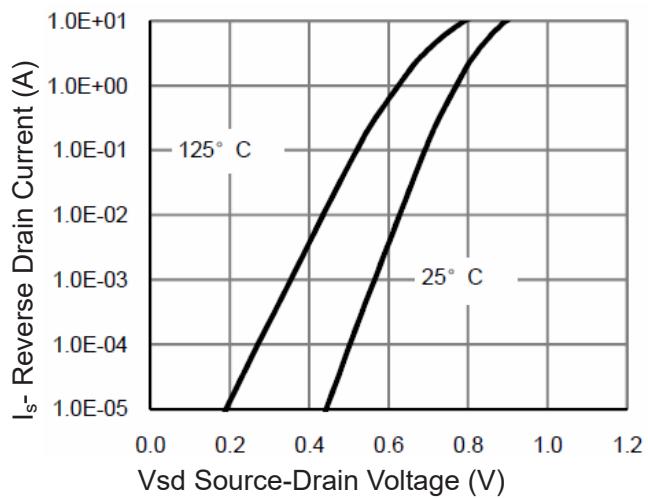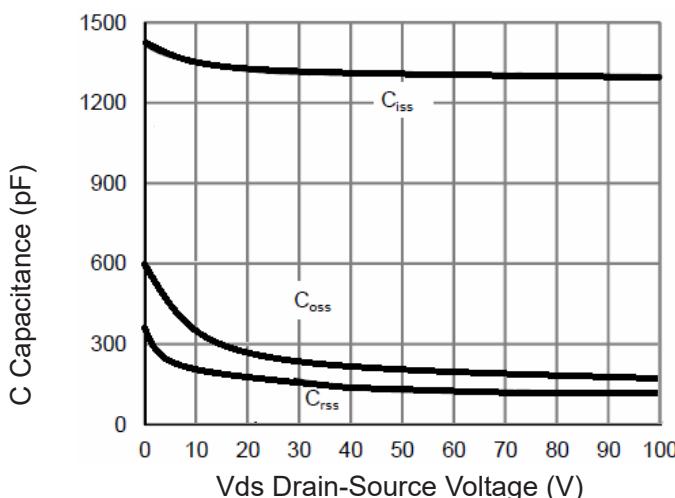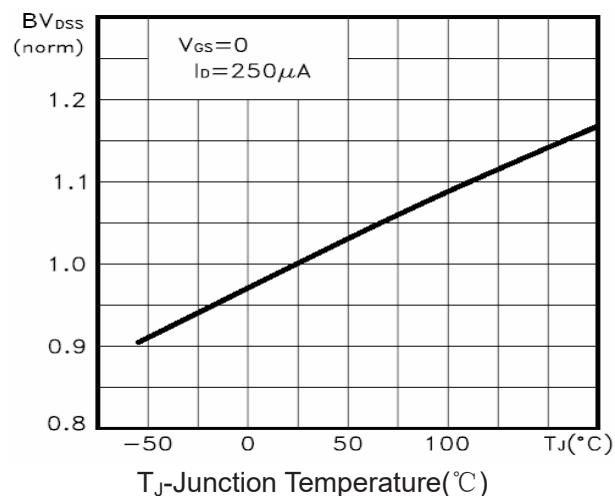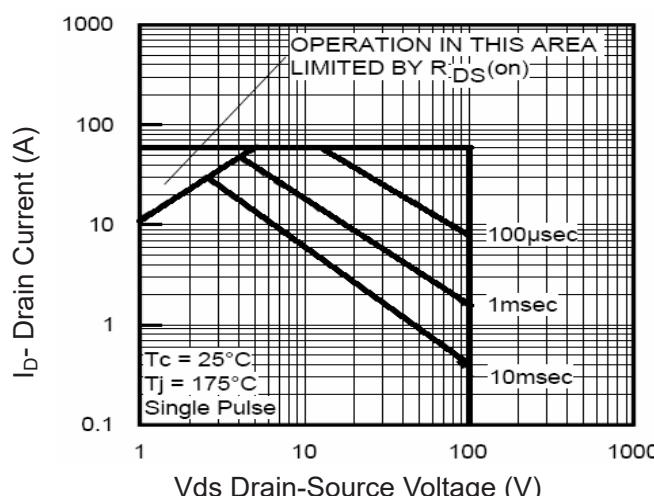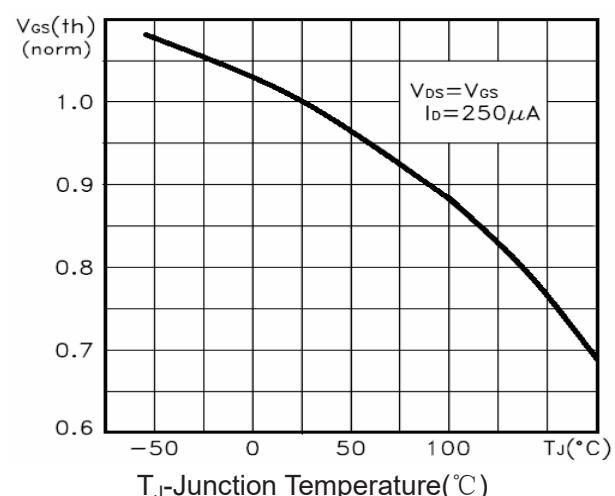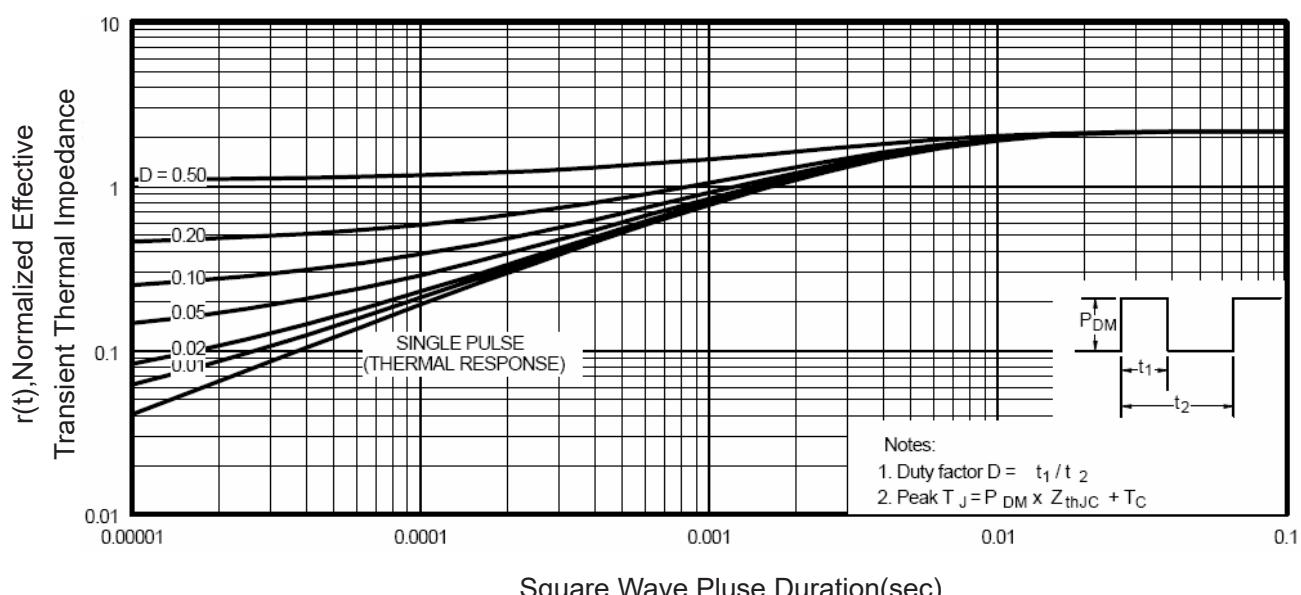
Figure 6 Source- Drain Diode Forward

Figure 7 Capacitance vs Vds

Figure 9   BV$_{DSS}$ vs Junction Temperature

Figure 8 Safe Operation Area

Figure 10 V$_{GS(th)}$ vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance